

Title (en)

RESISTOR DEVICE AND MANUFACTURING METHOD THEREOF

Title (de)

WIDERSTANDSVORRICHTUNG UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

RÉSISTANCE À COUCHE MINCE ET SON PROCÉDÉ DE FABRICATION

Publication

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Application

EP 16183502 A 20160810

Priority

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Abstract (en)

The present invention provides a wafer resistor device and a manufacturing method thereof. The manufacturing method of the wafer resistor device comprises the following steps: a first cutting step of magnetically attracting a magnetic metal contact of the wafer resistor device to cut a resistive layer for a first time; a second step of magnetically attracting the magnetic metal contact of the wafer resistor device to cut the resistive layer for a second time. Through the above steps, each wafer resistor device is heading in the same direction during the cutting steps to allow the cutting marks to appear in the same position on each wafer resistor device to reduce the amount of variation of the resistance value of each resistor due to the cutting steps.

IPC 8 full level

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CPC (source: EP)

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Citation (search report)

- [XAI] US 2014333411 A1 20141113 - YONEDA MASAKI [JP]
- [XI] US 2004164841 A1 20040826 - SAITO DAISUKE [JP], et al
- [A] US 2330782 A 19430928 - JAMES MORELOCK OLIVER
- [A] US 2011128115 A1 20110602 - LIAO CHIN-CHUNG [TW]
- [A] US 3063346 A 19621113 - LLOYD HAROLD E, et al
- [A] US 2004202227 A1 20041014 - NELSON CHARLES SCOTT [US], et al

Cited by

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